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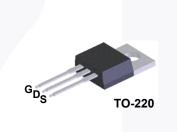
## FQP55N10 N-Channel QFET<sup>®</sup> MOSFET 100 V, 55 A, 26 mΩ

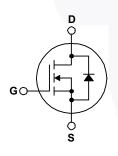
## Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

## Features

- 55 A, 100 V,  $R_{DS(on)}$  = 26 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_{D}$  = 27.5 A
- Low Gate Charge (Typ. 75 nC)
- Low Crss (Typ. 130 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

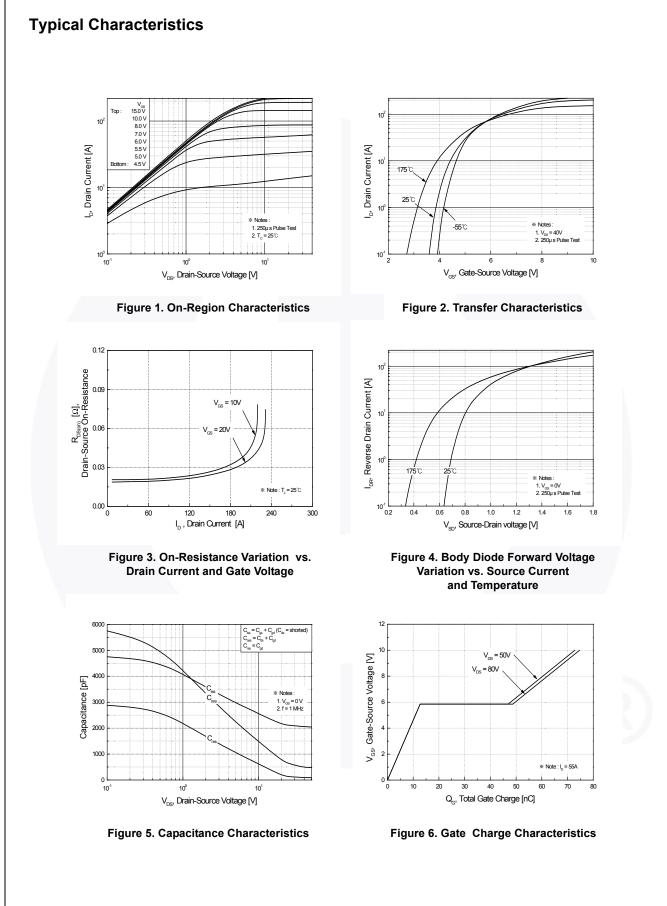
Symbol	Parameter		FQP55N10	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		100	V	
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )		55	A	
	- Continuous (T <sub>C</sub> = 100°C)	-	38.9	A	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	220	A	
V <sub>GSS</sub>	Gate-Source Voltage		± 25	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	1100	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	55	A	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	15.5	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns	
P <sub>D</sub>	Power Dissipation ( $T_C = 25^{\circ}C$ )		155	W	
- Derate above 25°C		-	1.03	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C	
TI	Maximum Lead Temperature for Soldering,		300	°C	
'L	1/8" from Case for 5 seconds		300	C	

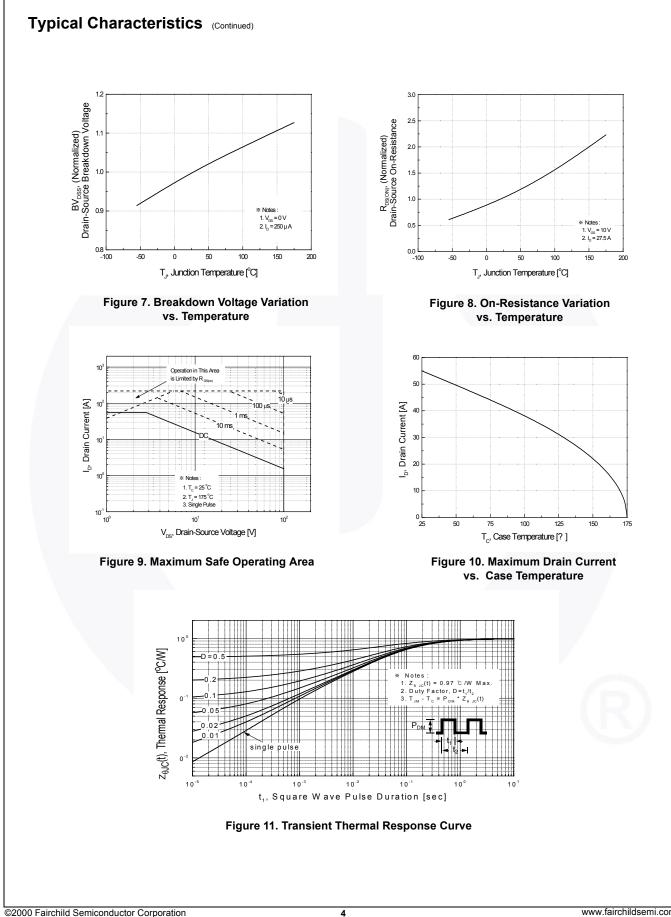
## **Thermal Characteristics**

Symbol	Parameter	FQP55N10	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.97	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

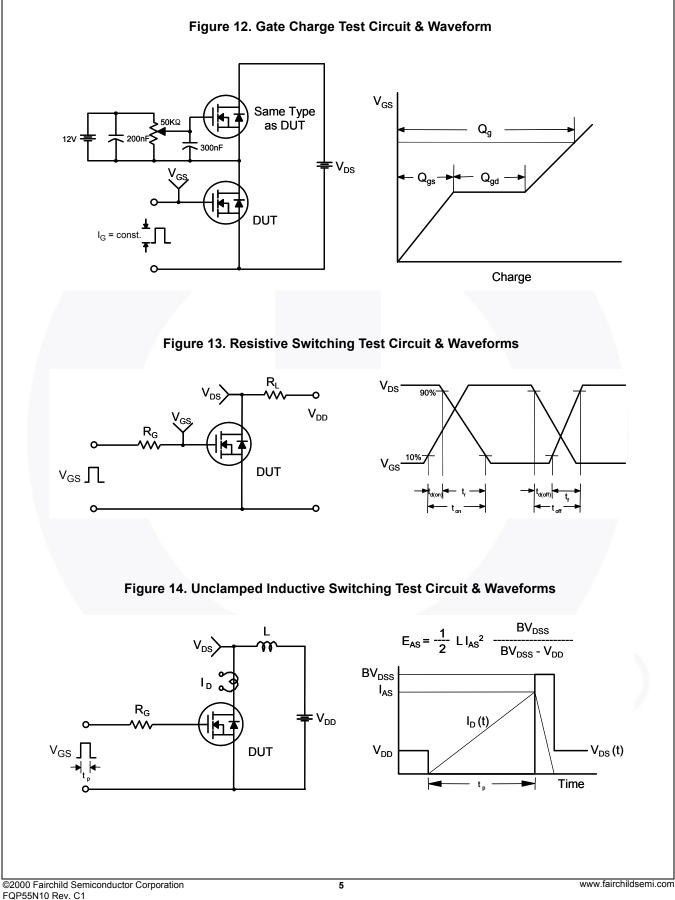
November 2013

Part N	Number	Top Mark	Package	Packing Method	Reel Size	Та	pe Widt	h Q	uantity	
	55N10	FQP55N10	TO-220	Tube	N/A		N/A		50 units	
lectri	cal Chai	racteristics T <sub>c</sub> = 25	°C unless otherv	vise noted.				I		
Symbol		Parameter		Test Conditions		Min	Тур	Max	Unit	
Off Cha	aracteristi	ics								
BV <sub>DSS</sub>	Drain-Sou	rce Breakdown Voltage	V <sub>GS</sub> = 0 '	V, I <sub>D</sub> = 250 μA		100			V	
ΔBV <sub>DSS</sub>	Breakdowi Coefficient	n Voltage Temperature	I <sub>D</sub> = 250	μA, Referenced to 25	°C		0.1		V/°C	
			V <sub>DS</sub> = 10	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V				1	μA	
	Zero Gate Voltage Drain Current			$V_{\rm DS} = 80 \text{ V}, \text{ T}_{\rm C} = 150^{\circ}\text{C}$				10	μA	
I <sub>GSSF</sub>	Gate-Body	Leakage Current, Forward		5 V, V <sub>DS</sub> = 0 V				100	nA	
I <sub>GSSR</sub>	-	Leakage Current, Reverse		5 V, V <sub>DS</sub> = 0 V				-100	nA	
On Cha	aracteristi	cs					1			
V <sub>GS(th)</sub>	1	shold Voltage	$V_{DS} = V_{C}$	<sub>SS</sub> , I <sub>D</sub> = 250 μA		2.0		4.0	V	
R <sub>DS(on)</sub>	Static Drai On-Resista	n-Source		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 27.5 \text{ A}$			0.021	0.026	Ω	
9 <sub>FS</sub>		ransconductance	V <sub>DS</sub> = 40	V, I <sub>D</sub> = 27.5 A			38		S	
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capa Output Ca Reverse T		V <sub>DS</sub> = 25 f = 1.0 M	s V, V <sub>GS</sub> = 0 V, Hz			2100 640 130	2730 830 170	pF pF pF	
Switchi	ing Chara	cteristics								
t <sub>d(on)</sub>	Turn-On D						25	60	ns	
t <sub>r</sub>	Turn-On R			$V_{DD} = 50 \text{ V}, \text{ I}_{D} = 55 \text{ A},$			250	510	ns	
t <sub>d(off)</sub>	Turn-Off D	elay Time	R <sub>G</sub> = 25	<u>(</u> 2			110	230	ns	
f	Turn-Off F	,		(Note 4)			140	290	ns	
Q <sub>g</sub>	Total Gate	Charge	$V_{DS} = 80$	$V_{DS}$ = 80 V, I <sub>D</sub> = 55 A, $V_{GS}$ = 10 V (Note 4)			75	98	nC	
Q <sub>gs</sub>	Gate-Sour						13		nC	
Q <sub>gd</sub>	Gate-Drair	n Charge	0				36		nC	
	Source Die	ode Characteristics a	and Maxir	num Ratings		1	1		1	
I <sub>S</sub>	1	Continuous Drain-Source D		-				55	Α	
I <sub>SM</sub>		Pulsed Drain-Source Diode						220	A	
V <sub>SD</sub>	Drain-Sou	rce Diode Forward Voltage	V <sub>GS</sub> = 0 '	$V_{GS} = 0 V, I_{S} = 55 A$				1.5	V	
t <sub>rr</sub>	Reverse R	ecovery Time		$V_{GS} = 0 V, I_S = 55 A,$ $dI_F / dt = 100 A/\mu s$			100		ns	
Q <sub>rr</sub>	Reverse R	ecovery Charge	dl <sub>F</sub> / dt =				380		nC	





FQP55N10 — N-Channel QFET<sup>®</sup> MOSFET



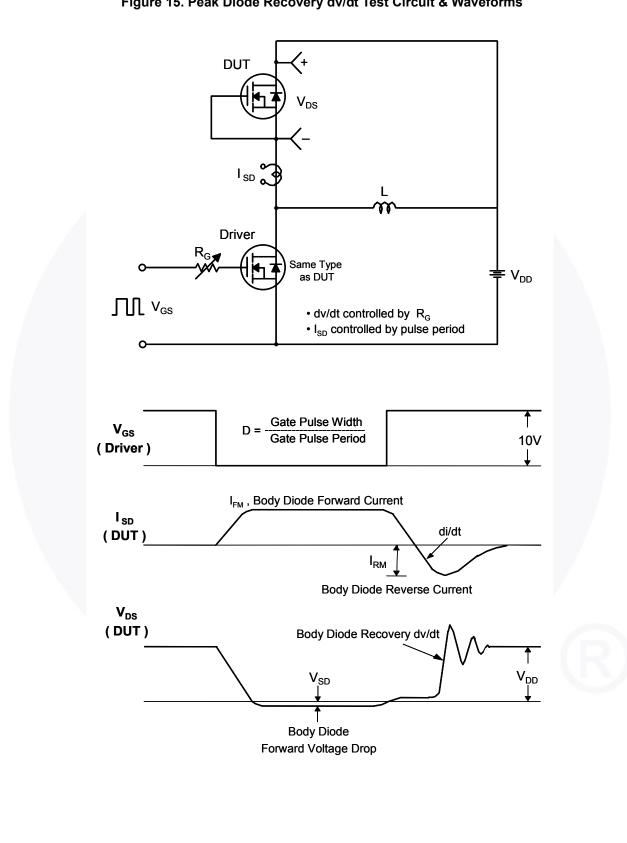
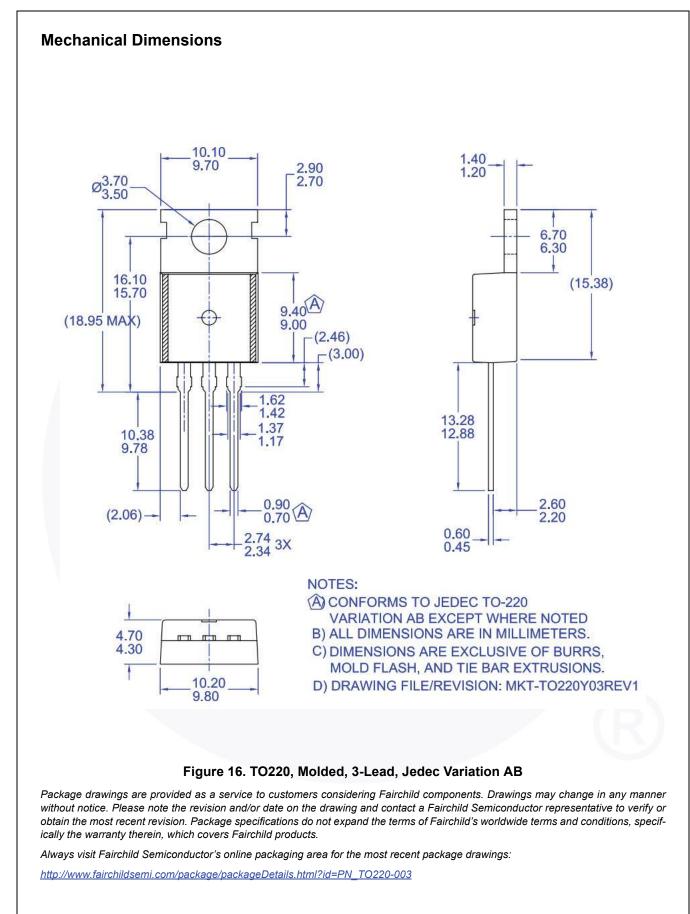


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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